

ABSTRACT OF THE DISCLOSURE

A semiconductor device, which can prevent a current capability from deteriorating with time, is disclosed. A P-channel type LDMOS is formed in an N-type monocrystal silicon substrate. The P-channel type LDMOS includes: a P-type impurity diffusion layer formed in a well shape so as to reach a predetermined depth; a channel well layer formed by double-diffusing N-type impurities; a source diffusion layer; a potential fixing electrode; drain-contact electrode; a LOCOS oxide film; a gate electrode; a drain electrode; a source electrode; and so on. Especially, the gate electrode is formed so as to overlap onto the LOCOS oxide film, and its protrusion amount onto the LOCOS oxide film (gate overlap length O/L) is set to about $10 \mu\text{m}$, which is substantially 1/2 of a width size of the LOCOS oxide film.

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